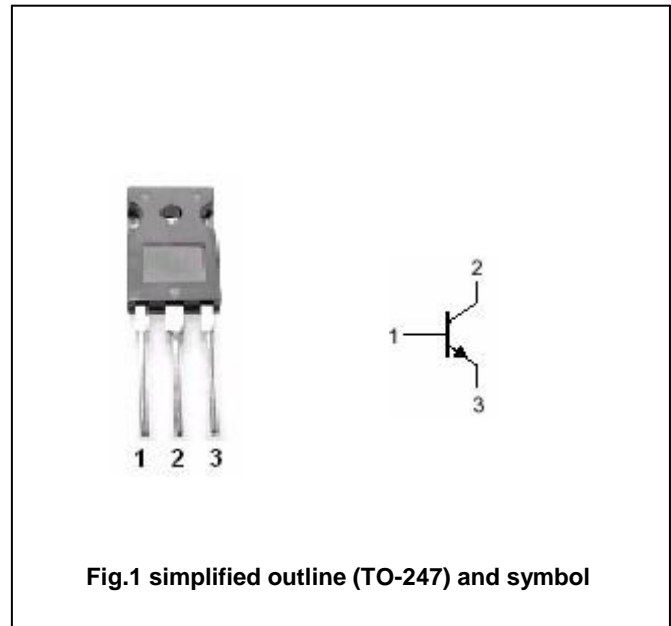


DESCRIPTION

- With TO-247 package
- Switching power transistor
- High breakdown voltage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	1200	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		6	A
I _{CM}	Collector current-Peak		12	A
I _B	Base current		3	A
I _{BM}	Base current-Peak		6	A
P _D	Total power dissipation	T _C =25	100	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-C}$	Thermal resistance junction to case	1.25	/W

CHARACTERISTICS

 $T_j=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.2A; I_B=0$	800			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3A; I_B=0.6A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=3A; I_B=0.6A$			1.5	V
I_{CBO}	Collector cut-off current	At rated voltage			0.1	mA
I_{CEO}	Collector cut-off current					
I_{EBO}	Emitter cut-off current	At rated voltage			0.1	mA
h_{FE-1}	DC current gain	$I_C=3A; V_{CE}=5V$	8			
h_{FE-2}	DC current gain	$I_C=1mA; V_{CE}=5V$	7			
f_T	Transition frequency	$I_C=0.6A; V_{CE}=10V$		8		MHz
Switching times resistive load						
t_{on}	Turn-on time	$I_C=3A$ $I_{B1}=0.6A; I_{B2}=1.2A$ $V_{BB2}=4V, R_L=85\Omega$			0.5	μs
t_s	Storage time				3.5	μs
t_f	Fall time				0.3	μs

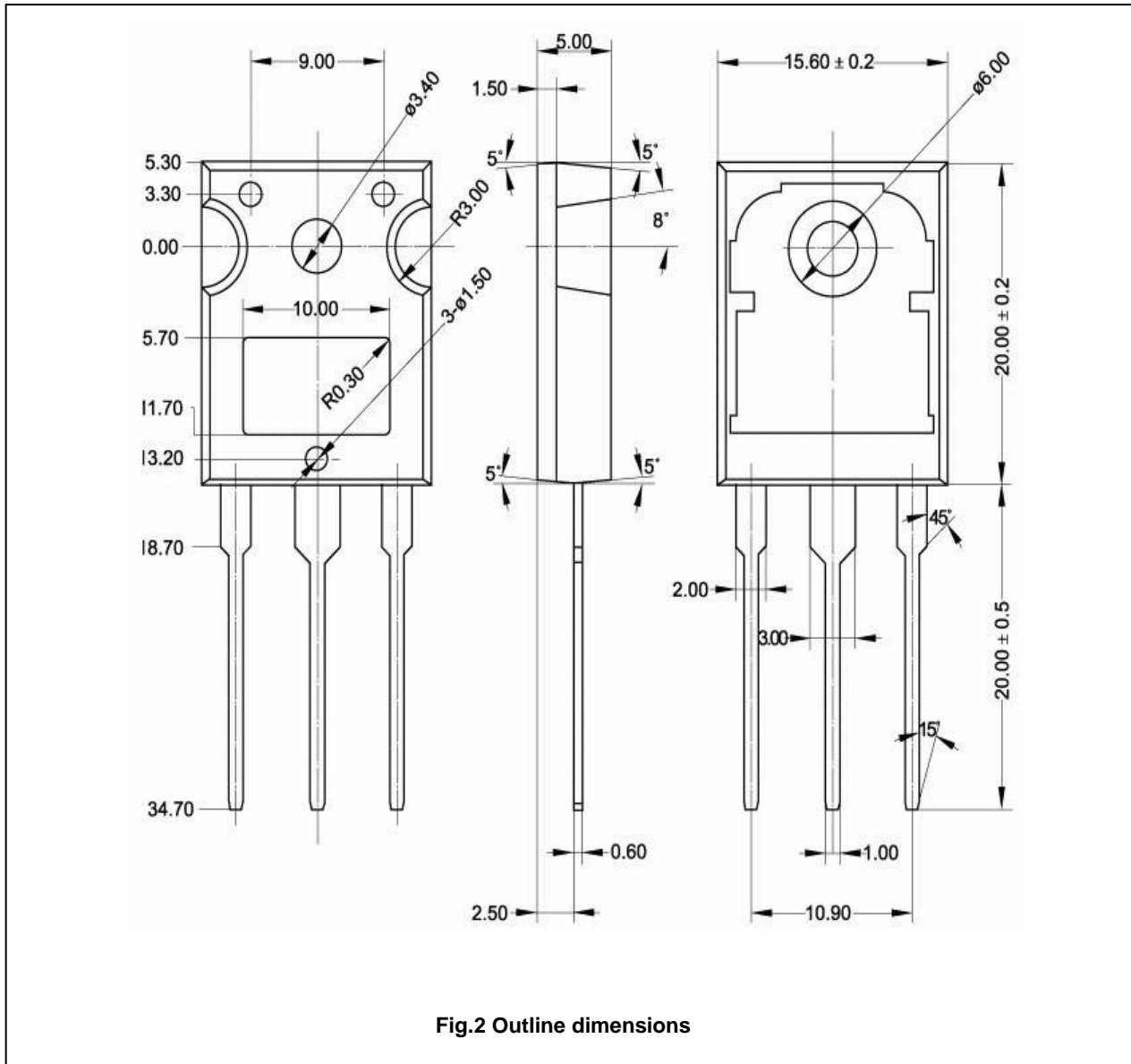


Fig.2 Outline dimensions